MOSFETs Silicon Carbide N-Channel MOS

# TW031V65C

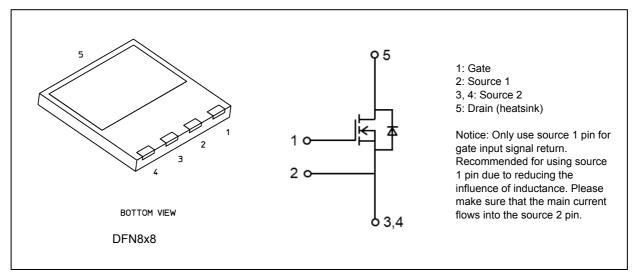
### 1. Applications

• Switching Voltage Regulators

#### 2. Features

- (1) Chip design of 3rd generation (Built-in SiC schottky barrier diode)
- (2) Low diode forward voltage:  $V_{DSF}$  = -1.35 V (typ.)
- (3) High voltage:  $V_{DSS} = 650 \text{ V}$
- (4) Low drain-source on-resistance:  $R_{DS(ON)} = 31 \text{ m}\Omega$  (typ.)
- (5) Less susceptible to malfunction due to high threshold voltage:  $V_{th}$  = 3.0 to 5.0 V ( $V_{DS}$  = 10 V,  $I_D$  = 3 mA)
- (6) Recommended gate source drive voltage:  $V_{GS_{on}} = 18 \text{ V}, V_{GS_{off}} = 0 \text{ V}$
- (7) Enhancement mode.

### 3. Packaging and Internal Circuit



### 4. Absolute Maximum Ratings (Note) ( $T_a = 25 \ ^{\circ}C$ unless otherwise specified)

|                        | Characteristics            | Symbol   | Rating           | Unit       |    |
|------------------------|----------------------------|----------|------------------|------------|----|
| Drain-source voltage   |                            |          | V <sub>DSS</sub> | 650        | V  |
| Gate-source voltage    |                            |          | V <sub>GSS</sub> | +25/-10    |    |
| Drain current (DC)     | ( T <sub>c</sub> = 25 °C ) | (Note 1) | Ι <sub>D</sub>   | 53         | A  |
| Drain current (DC)     | ( T <sub>c</sub> = 100°C ) | (Note 1) | Ι <sub>D</sub>   | 38         |    |
| Drain current (pulsed) | ( T <sub>c</sub> = 25 °C ) | (Note 1) | I <sub>DP</sub>  | 163        |    |
| Drain current (pulsed) | ( T <sub>c</sub> = 100°C ) | (Note 1) | I <sub>DP</sub>  | 122        |    |
| Power dissipation      | ( T <sub>c</sub> = 25°C )  |          | PD               | 156        | w  |
| Channel temperature    |                            |          | T <sub>ch</sub>  | 175        | °C |
| Storage temperature    |                            |          | T <sub>stg</sub> | -55 to 175 |    |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### 5. Thermal Characteristics

| Characteristics                    | Symbol                | Max   | Unit |
|------------------------------------|-----------------------|-------|------|
| Channel-to-case thermal resistance | R <sub>th(ch-c)</sub> | 0.961 | °C/W |

Note 1: Ensure that the channel temperature does not exceed 175 °C.

Note: This transistor is sensitive to electrostatic discharge and should be handled with care. It should be used for switching applications.

## 6. Electrical Characteristics

## 6.1. Static Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

| Characteristics                   |          | Symbol               | Test Condition   | Min | Тур. | Max  | Unit |
|-----------------------------------|----------|----------------------|--|-----|------|------|------|
| Gate leakage current              |          | I <sub>GSS</sub>     | V <sub>GS</sub> = +25/-10 V, V <sub>DS</sub> = 0 V                         | _   | _    | ±0.1 | μA   |
| Drain cut-off current             |          | I <sub>DSS</sub>     | V <sub>DS</sub> = 650 V, V <sub>GS</sub> = 0 V                             |     | 7.0  | 100  |      |
|                                   |          |                      | T <sub>a</sub> = 150 °C,<br>V <sub>DS</sub> = 650 V, V <sub>GS</sub> = 0 V | —   | 37   | —    |      |
| Drain-source breakdown<br>voltage |          | V <sub>(BR)DSS</sub> | I <sub>D</sub> = 4 mA, V <sub>GS</sub> = 0 V                               | 650 | _    | —    | V    |
| Gate threshold voltage            | (Note 2) | V <sub>th</sub>      | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 3 mA                              | 3.0 | _    | 5.0  |      |
| Drain-source on-resistance        |          | R <sub>DS(ON)</sub>  | V <sub>GS</sub> = 18 V, I <sub>D</sub> = 29 A                              |     | 31   | 45   | mΩ   |
|                                   |          |                      | T <sub>a</sub> = 150 °C,<br>V <sub>GS</sub> = 18 V, I <sub>D</sub> = 29 A  | _   | 35   | _    |      |

Note 2: Please be sure to apply  $I_{GSS}$  ( $V_{GS}$  = 25 V) before the  $V_{th}$  test.

## 6.2. Dynamic Characteristics (Ta = 25 °C unless otherwise specified)

| Characteristics                               | Symbol              | Test Condition                                  | Min | Тур. | Max | Unit |
|---|---------------------|---|-----|------|-----|------|
| Input capacitance                             | C <sub>iss</sub>    | V <sub>DS</sub> = 400 V, V <sub>GS</sub> = 0 V, | _   | 2288 | _   | pF   |
| Reverse transfer capacitance                  | C <sub>rss</sub>    | ]f = 100 kHz                                    | _   | 6.6  | —   |      |
| Output capacitance                            | C <sub>oss</sub>    | ]   | _   | 249  | _   |      |
| Effective output capacitance (energy related) | C <sub>o(er)</sub>  | -<br>-<br>-                                     | —   | 288  | —   |      |
| Effective output capacitance (time related)   | C <sub>o(tr)</sub>  |   | —   | 413  | —   |      |
| Output charge                                 | Q <sub>oss</sub>    |   |     | 165  | _   | nC   |
| C <sub>oss</sub> stored energy                | E <sub>oss</sub>    |   | _   | 23   | _   | μJ   |
| Gate resistance                               | r <sub>g</sub>      | V <sub>DS</sub> = OPEN, f = 1 MHz               |     | 2.1  | _   | Ω    |
| Turn-on delay time                            | t <sub>d(on)</sub>  | See Fig. 6.2.1                                  | _   | 30   | —   | ns   |
| Switching time (rise time)                    | t <sub>r</sub>      |   | _   | 15   | _   |      |
| Turn-off delay time                           | t <sub>d(off)</sub> |   | _   | 42   | _   |      |
| Switching time (fall time)                    | t <sub>f</sub>      |   |     | 18   | _   |      |
| Turn-on switching loss                        | Eon                 |   |     | 163  |     | μJ   |
| Turn-off switching loss                       | E <sub>off</sub>    | ]   | _   | 100  | _   | ]    |

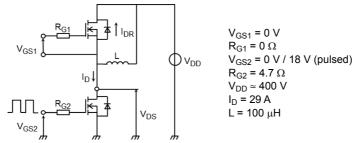


Fig. 6.2.1 Switching Time Test Circuit

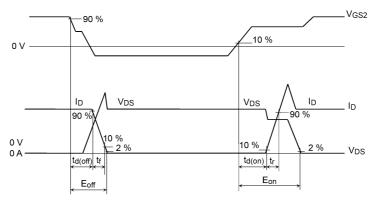


Fig. 6.2.2 Timing Diagrams

## 6.3. Gate Charge Characteristics ( $T_a = 25$ °C unless otherwise specified)

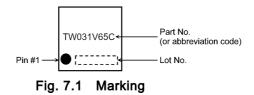
| Characteristics                                 | Symbol           | Test Condition   | Min | Тур. | Max | Unit |
|---|------------------|--|-----|------|-----|------|
| Total gate charge (gate-source plus gate-drain) | Qg               | $V_{DD} \approx 400 \text{ V}, \text{ V}_{GS}$ = 18 V,<br>I_D = 29 A | _   | 65   | _   | nC   |
| Gate-source charge 1                            | Q <sub>gs1</sub> |  | —   | 26   | —   |      |
| Gate-drain charge                               | Q <sub>gd</sub>  |  |     | 10   | _   |      |

## 6.4. Source $\cdot$ Drain Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

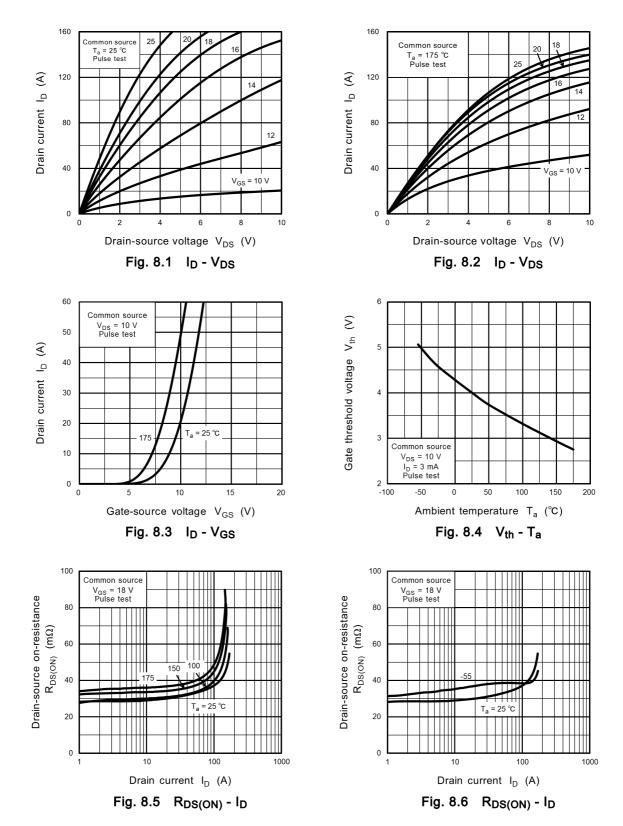
| Characteristics                  |          | Symbol           | Test Condition   | Min | Тур.  | Max   | Unit |
|----------------------------------|----------|------------------|--|-----|-------|-------|------|
| Reverse drain current (DC)       | (Note 3) | I <sub>DR</sub>  | T <sub>c</sub> = 25 °C, V <sub>GS</sub> = -5 V                             | _   | _     | 44    | А    |
|                                  |          |                  | T <sub>c</sub> = 100 °C, V <sub>GS</sub> = -5 V                            |     |       | 29    |      |
|                                  |          |                  | T <sub>c</sub> = 25 °C, V <sub>GS</sub> = 18 V                             | _   | —     | 53    |      |
|                                  |          |                  | T <sub>c</sub> = 100 °C, V <sub>GS</sub> = 18 V                            |     |       | 38    |      |
| Reverse drain current            | (Note 3) | I <sub>DRP</sub> | T <sub>c</sub> = 25 °C, V <sub>GS</sub> = -5 V                             |     |       | 163   |      |
| (pulsed)                         |          |                  | T <sub>c</sub> = 100 °C, V <sub>GS</sub> = -5 V                            | _   | _     | 75    |      |
|                                  |          |                  | T <sub>c</sub> = 25 °C, V <sub>GS</sub> = 18 V                             |     | _     | 163   |      |
|                                  |          |                  | T <sub>c</sub> = 100 °C, V <sub>GS</sub> = 18 V                            |     |       | 122   |      |
| Diode forward voltage            |          | V <sub>DSF</sub> | I <sub>DR</sub> = 21 A, V <sub>GS</sub> = -5 V                             |     | -1.35 | -1.80 | V    |
|                                  |          |                  | T <sub>a</sub> = 150 °C,<br>I <sub>DR</sub> = 21 A, V <sub>GS</sub> = -5 V | —   | -1.57 | —     |      |
| Reverse recovery time            |          | t <sub>rr</sub>  | I <sub>DR</sub> = 19 A, V <sub>GS</sub> = 0 V,                             |     | 55    | _     | ns   |
| Reverse recovery charge          |          | Q <sub>rr</sub>  | V <sub>DD</sub> = 400 V, -dI <sub>DR</sub> /dt = 1000 A/μs                 | _   | 358   | —     | nC   |
| Peak reverse recovery<br>current |          | I <sub>rr</sub>  |  | —   | 13    | _     | A    |

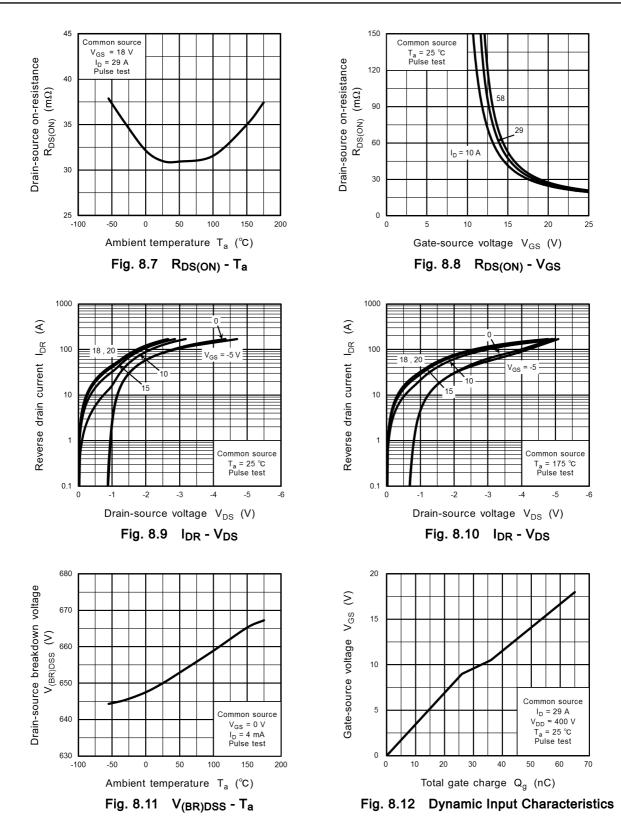
Note 3: Ensure that the channel temperature does not exceed 175 °C.

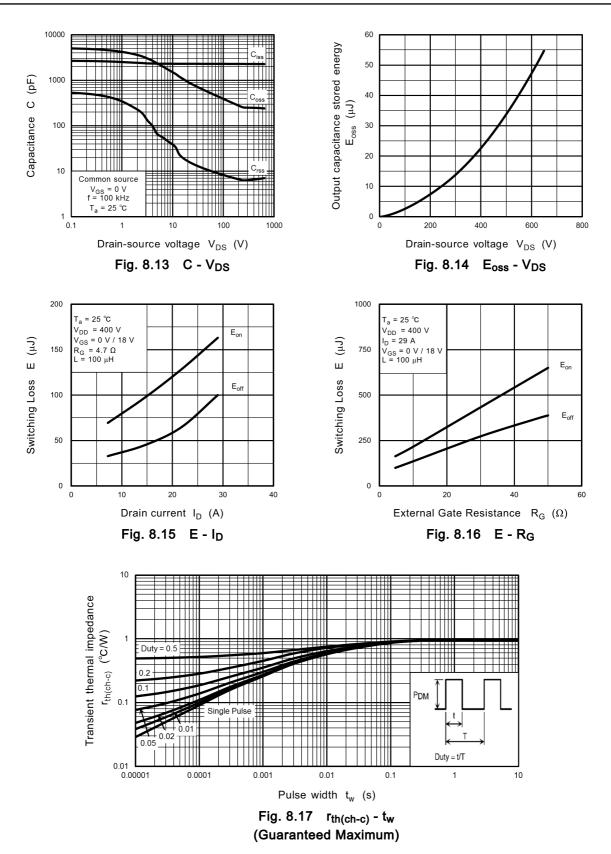
## 7. Marking



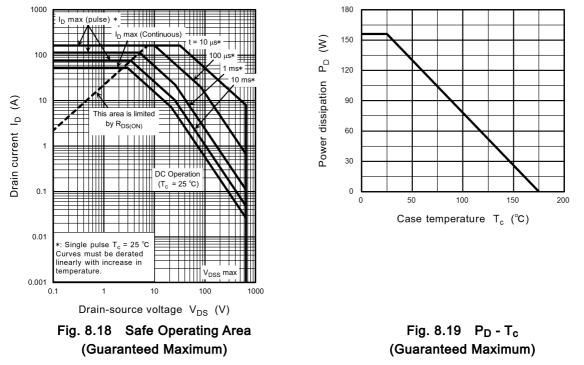
## 8. Characteristics Curves (Note)











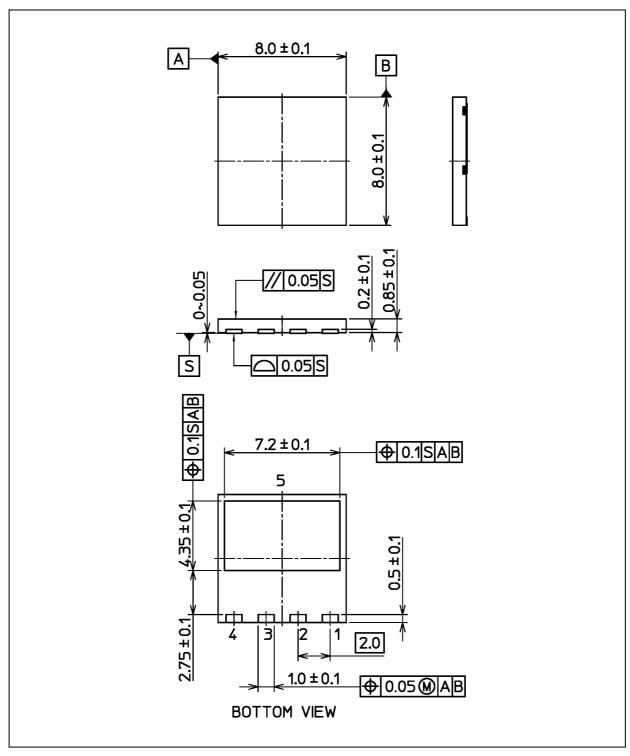
Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



## TW031V65C

#### **Package Dimensions**

Unit: mm



Weight: 0.175 g (typ.)

Package Name(s)

TOSHIBA: 2-8T1A

Nickname: DFN8x8

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